	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	2	6680514.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:08
2	BRS	27	("5196373" "5208170" "5674781" "5705857" "5831899" "5850096" "5877557" "5895261" "5899742" "5907781" "5920098" "5920796" "5930669" "5965924" "5970375" "5976975" "5990524" "6018180" "6051881" "6121659" "6180506" "6184143" "6323554" "6333229" "6333557" "6521977" "6576550" "2001/0055840").PN.	USPAT	2004/11/05 11:44
3	BRS	0	6680514.URPN.	USPAT	2004/11/05 11:45
4	BRS	739	438/652.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:11
5	BRS	1297	438/118.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
6	BRS	2206	438/622.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
7	BRS	993	438/618.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
8	BRS	568	438/666.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
9	BRS	717	438/629.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
10	BRS	2063	438/637.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12
11	BRS	535	438/639.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:12

	Type	Hits	Search Text	DBs	Time Stamp
12	BRS	412	438/640.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
13	BRS	257	438/667.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
14	BRS	180	438/668.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
15	BRS	927	438/672.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
16	BRS	588	438/675.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
17	BRS	849	438/700.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
18	BRS	706	438/701.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:13
19	BRS	879	438/978.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:14
20	BRS	261	438/713.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 12:40
21	BRS	2	substrate with (transistor or FET) and (passivat$4 or SiN or SiC) with (transistor or FET) and (passivat$4 or SiN or SiC) with (insulat$4 or PSG or BPSG) and (insulat$4 or PSG or BPSG) with damascene adj conductive adj (wire or stud) and capping with damascene adj conductive adj (wire or stud) and dual adj damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:16
22	BRS	3	damascene adj conductive adj (wire or stud) and dual adj damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:13

	Type	Hits	Search Text	DBs	Time Stamp
23	BRS	10	substrate with (transistor or FET) and capping with damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:15
24	BRS	222	capping with damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 14:26
25	BRS	5	damascene adj conductive adj (wire or wiring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:17
26	BRS	40	("6051881" "6018180" "5990524" "5976975" "5970375" "5965924" "5930669" "5920098" "5907781" "5899742" "5895261" "5850096" "5831899" "5674781" "5208170" "5196373" "5705857" "6018180" "6333557" "6180506" "6333229").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 13:18
27	BRS	7	capping with damascene with (wire or stud)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 14:43
28	BRS	17	cap$4 with damascene with (wire or stud)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:35
29	BRS	2	5889328.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:00
30	BRS	659	(capacitor resistor inductor charge adj couple$2 light adj emitting ajd diode) with damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:36
31	BRS	8	(capacitor resistor inductor charge adj couple$2 light adj emitting ajd diode) with passivat$4 and passivat$4 with damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:39
32	BRS	659	(capacitor resistor inductor charge adj couple$2 light adj emitting ajd diode) with damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:39
33	BRS	257	(capacitor resistor inductor charge adj couple$2 light adj emitting ajd diode) with damascene with insulat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 16:39